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(54) **Title:** SPACER LED ARCHITECTURE FOR HIGH EFFICIENCY MICRO LED DISPLAYS

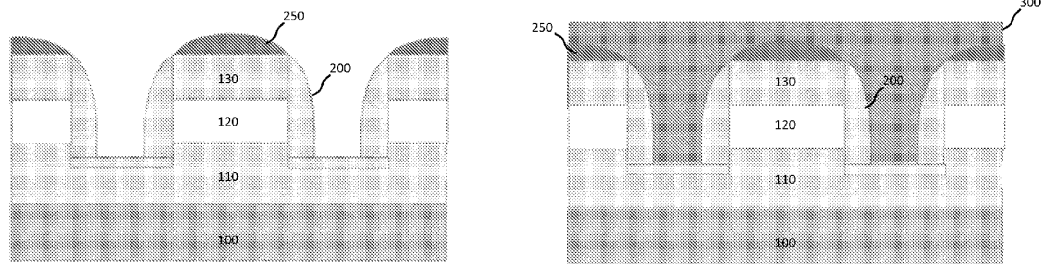


FIG. 7

(57) **Abstract:** A method of forming an optical device, the method comprising the steps of forming a mesa, the mesa comprising an active layer configured to emit light from a first light emitting surface of the mesa when subjected to an electrical current, the mesa further comprising a second surface opposite the light emitting surface and substantially vertical sidewalls, forming spacers on the mesa sidewalls, the spacers being formed from a first electrically insulating, optically transparent material, and having an internal face facing the mesa sidewalls, and an opposing external face, depositing a first layer of transparent conducting oxide on the light emitting surface of the mesa, the transparent conducting oxide having an internal face facing the second surface of the mesa, and an opposing external face, and depositing a layer of reflective, electrically conducting material over the transparent conducting oxide and external faces of the spacers.



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